



ACE2302C

N-Channel Enhancement Mode MOSFET

Description

The ACE2302C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as load switch or in PWM applications.

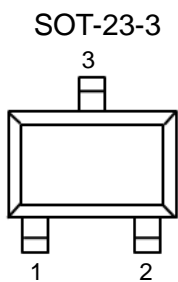
Features

- 20V/5.1A
- $R_{DS(ON)}=28m\Omega$ (typ.) @ $V_{GS}=4.5V$
- $R_{DS(ON)}=38m\Omega$ (typ.) @ $V_{GS}=2.5V$
- $R_{DS(ON)}=60m\Omega$ (typ.) @ $V_{GS}=1.8V$

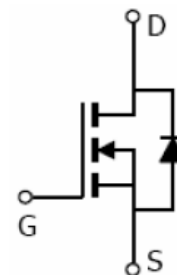
Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current (Continuous)	I_D	$T_A=25^\circ C$	5.1
		$T_A=70^\circ C$	4
Drain Current (Pulsed)	I_{DM}	20	A
Power Dissipation	$T_A=25^\circ C$	P_D	1
Operating temperature / storage temperature	T_J/T_{STG}	-55~150	$^\circ C$

Packaging Type



SOT-23-3	Description	Function
1	G	Gate
2	S	Source
3	D	Drain



Ordering information

ACE2302C XX + H

- └─ Halogen - free
- └─ Pb - free
- └─ BM : SOT-23-3



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Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	20	24		V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=250\mu\text{A}$	0.6	0.84	1	V
Gate leakage current	I_{GSS}	$V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$			100	nA
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=3\text{A}$		23	28	m Ω
		$V_{GS}=2.5\text{V}, I_D=2\text{A}$		31	38	
		$V_{GS}=1.8\text{V}, I_D=2\text{A}$		55	60	
Forward transconductance	g_{FS}	$V_{DS}=10\text{V}, I_D=6\text{A}$		5		S
Diode forward voltage	V_{SD}	$I_{SD}=1.7\text{A}, V_{GS}=0\text{V}$		0.9		V
Maximum body-diode continuous current	I_S				1.7	A
Switching						
Total gate charge	Q_g	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=6\text{A}$		6.3	8.1	nC
Gate-source charge	Q_{gs}			1.7	2.2	
Gate-drain charge	Q_{gd}			1.4	1.8	
Turn-on delay time	$t_{d(on)}$	$V_{GS}=10\text{V}, I_D=1\text{A}, R_G=6\Omega, V_{GS}=4.5\text{V}$		10.4	20.8	ns
Turn-on rise time	T_r			4.4	8.8	
Turn-off delay time	$t_{d(off)}$			27.4	54.8	
Turn-off fall time	T_f			4.2	8.4	
Dynamic						
Input capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=8\text{V}, f=1.0\text{MHz}$		522.3		pF
Output capacitance	C_{oss}			98.5		
Reverse transfer capacitance	C_{rss}			74.7		

Note :

- The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.
- Repetitive rating, pulse width limited by junction temperature.
- The current rating is based on the $t \leq 10\text{s}$ junction to ambient thermal resistance rating.



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Typical Performance Characteristics

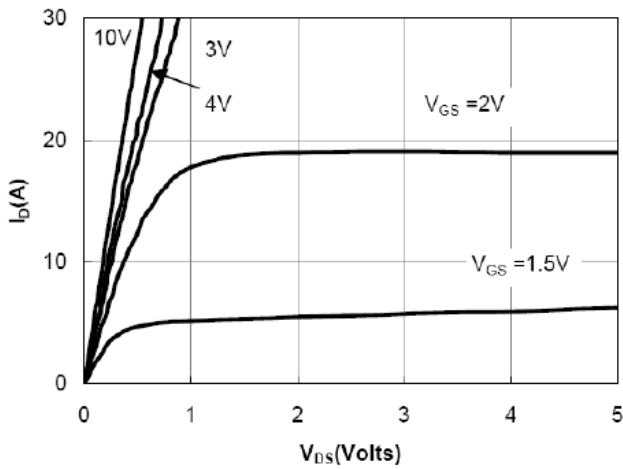


Figure 1: On-Regions Characteristics

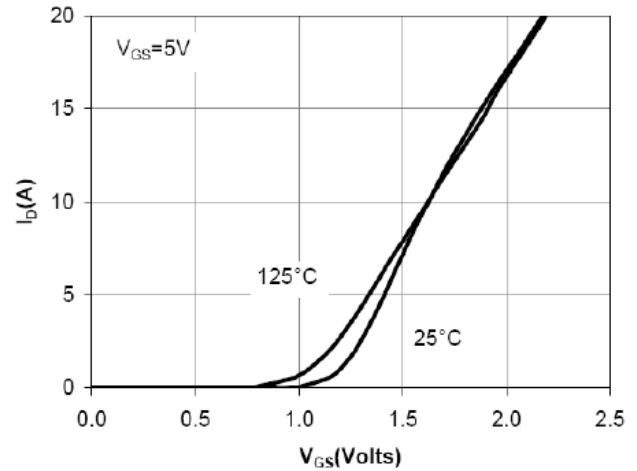


Figure 2: Transfer Characteristics

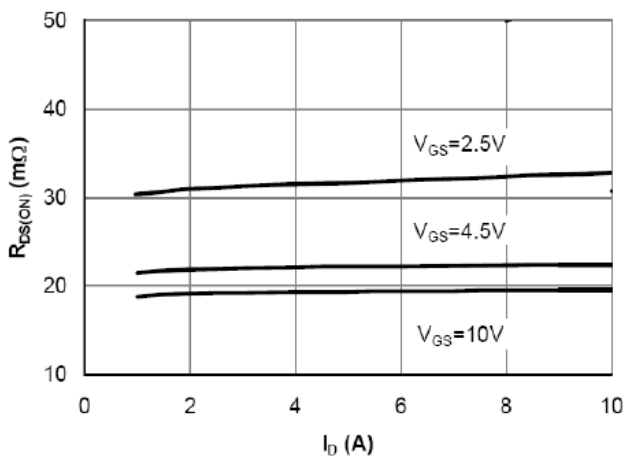


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

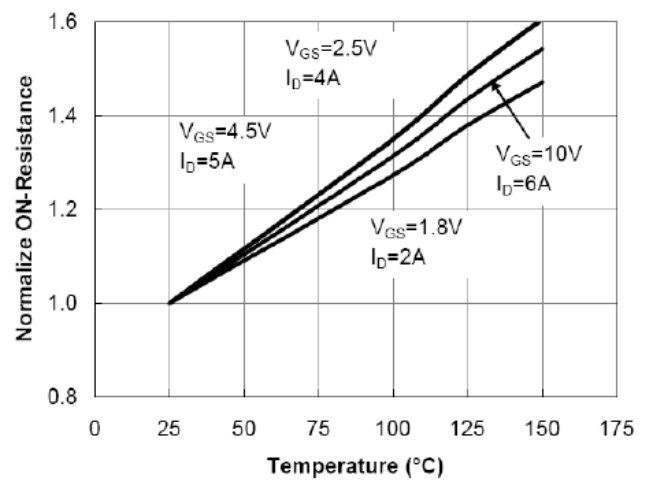


Figure 4: On-Resistance vs. Junction Temperature

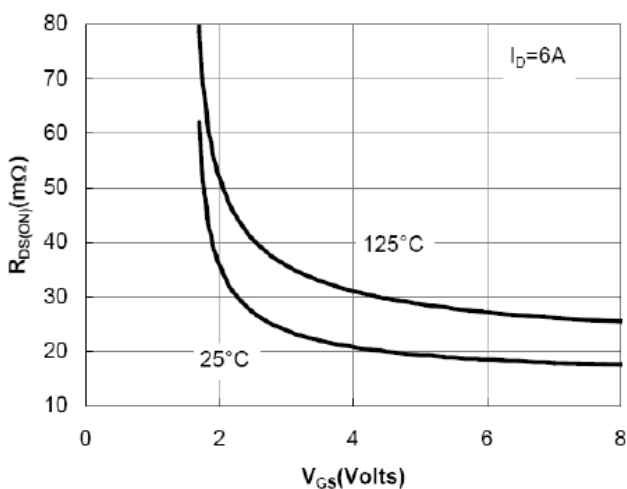


Figure 5: On-Resistance vs. Gate-Source Voltage

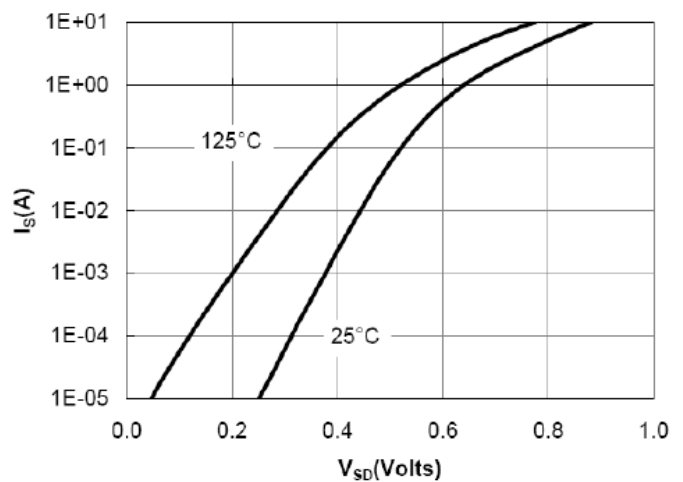


Figure 6: Body-Diode Characteristics



Typical Performance Characteristics

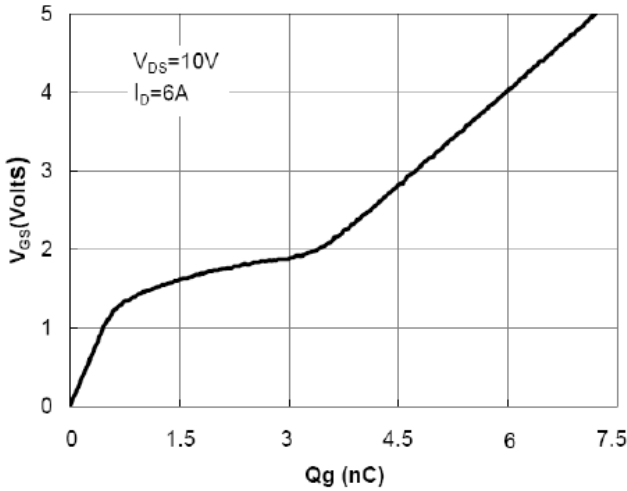


Figure 7: Gate-Charge Characteristics

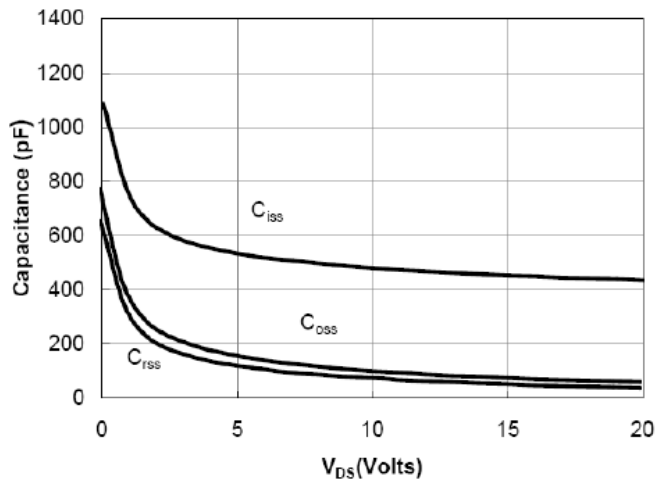


Figure 8: Capacitance Characteristics

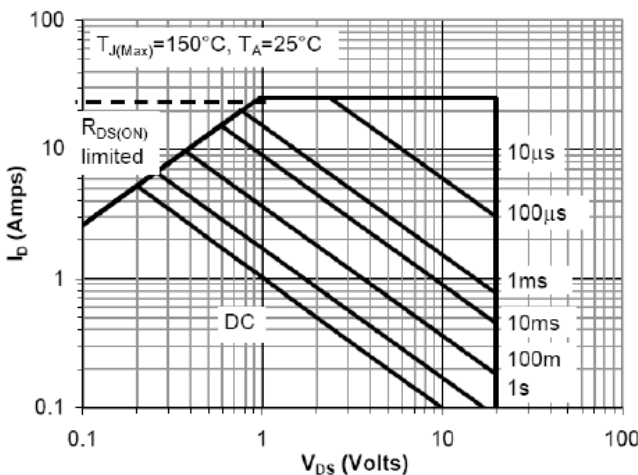


Figure 9: Maximum Forward Biased Safe Operating Area

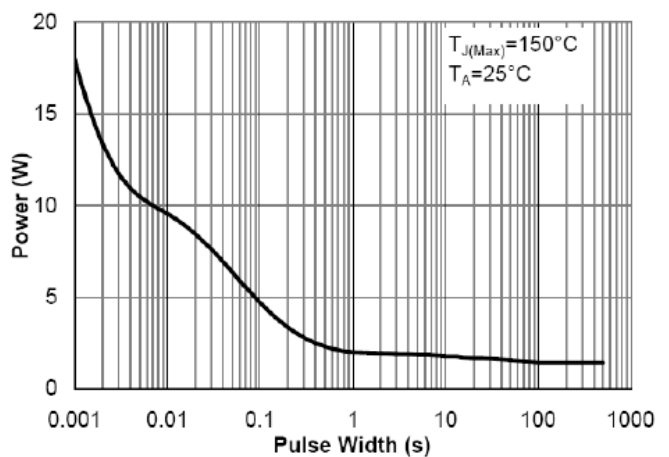


Figure 10: Single Pulse Power Rating Junction-to-Ambient

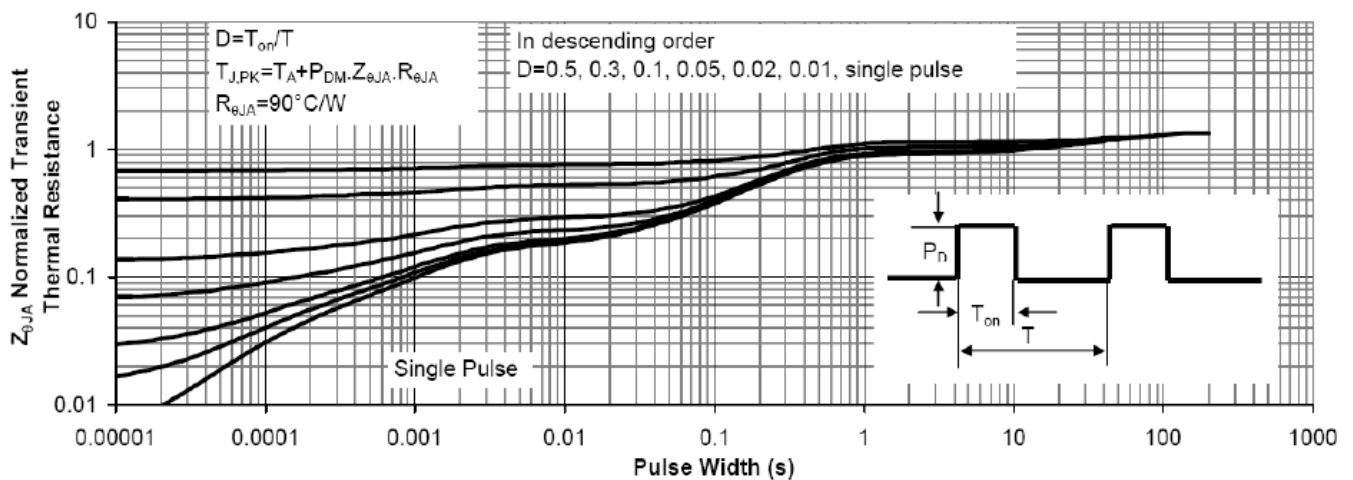


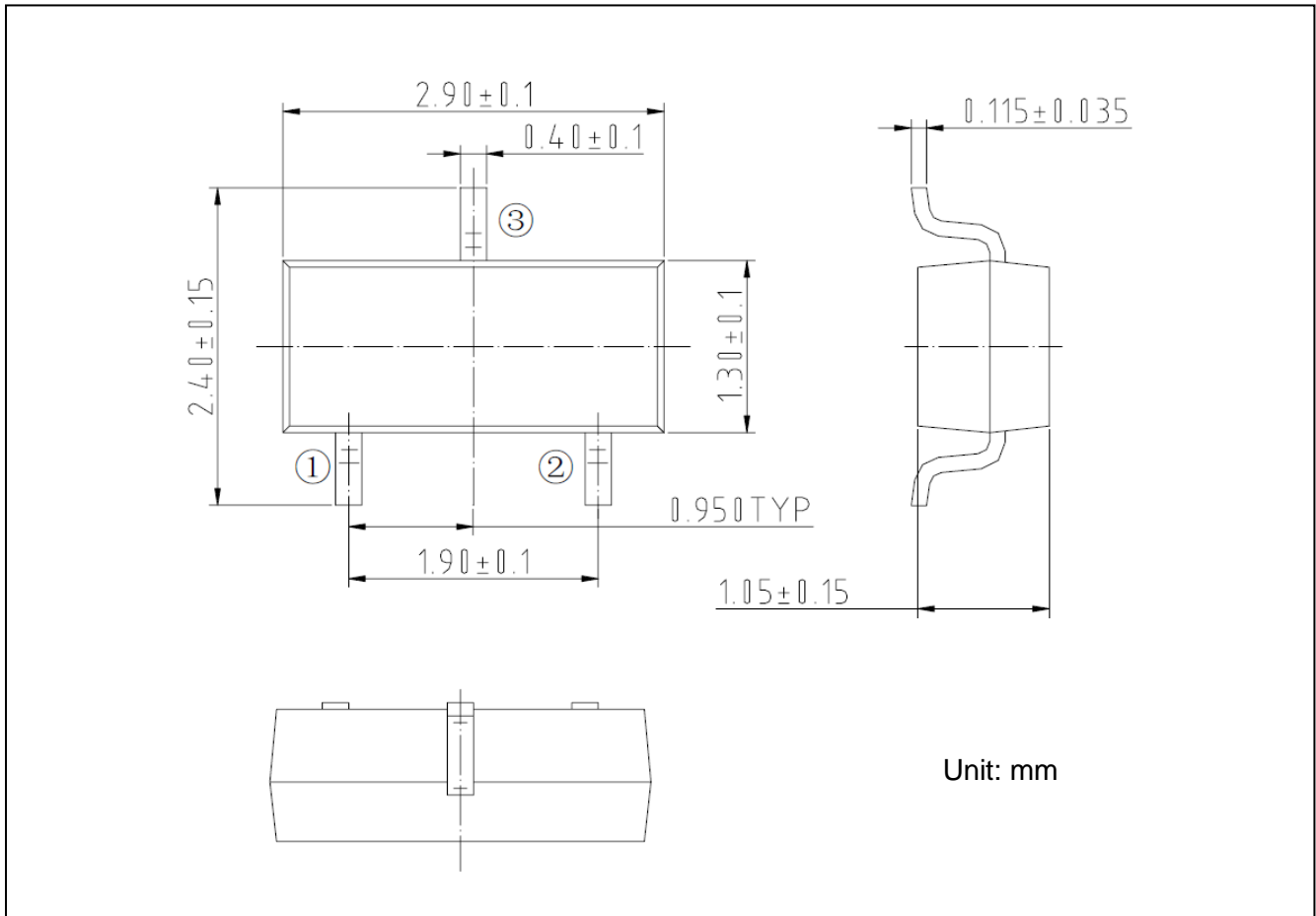
Figure 11: Normalized Maximum Transient Thermal Impedance



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Packing Information

SOT-23-3





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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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